

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI TVU 025 is Designed for

**FEATURES:**

- Input Matching Network
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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	8.0 A
<b>V<sub>CBO</sub></b>	45 V
<b>V<sub>CEO</sub></b>	30 V
<b>V<sub>EBO</sub></b>	3.0 V
<b>P<sub>DISS</sub></b>	135 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-50 °C to +200 °C
<b>T<sub>STG</sub></b>	-50 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.3 °C/W

**PACKAGE STYLE .450 BAL FLG(A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C	.785 / 19.94	
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N	.195 / 4.95	
P	.445 / 11.30	.455 / 11.56

**ORDER CODE: ASI10650**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 50 mA	45			V
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 200 mA	30			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	3.0			V
<b>I<sub>CEO</sub></b>	V <sub>CE</sub> = 25 V			5.0	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 3.0 A	10		80	---
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz		70		pF
<b>P<sub>G</sub></b> <b>IMD<sub>1</sub></b>	V <sub>CE</sub> = 25 V      I <sub>C</sub> = 3.2 A      f = 860 MHz P <sub>OUT</sub> = 25 W	8.0 -45			dB dBc